

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	-70 -55	А
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-3.0	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-120	Α
Avalanche Current (Notes 8) L = 1mH			I _{AS}	-16	Α
Avalanche Energy (Notes 8) L = 1mH			E _{AS}	130	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	105	°C/W
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P _D	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	45	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	3.0	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	V _{DS} = -24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	В	_	4.3	6	mΩ	$V_{GS} = -10V, I_D = -11.5A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	1	6.6	13		$V_{GS} = -4.5V, I_D = -8.5A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	1	2826	1	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	606	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	305	_	pF		
Gate Resistance	Rg	_	23	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	31.2	_	nC	V _{DS} = -15V, I _D = -11.5A	
Total Gate Charge (V _{GS} = -10V)	Qg	_	64.2	_	nC		
Gate-Source Charge	Q _{gs}	_	10.6	_	nC		
Gate-Drain Charge	Q _{gd}	_	11.6	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.8	_	ns	$V_{DD} = -15V$, $V_{GS} = -10V$, $R_g = 6\Omega$, $I_D = -11.5A$	
Turn-On Rise Time	t _R	_	4.3	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	306	_	ns		
Turn-Off Fall Time	t _F	_	125	_	ns		
Reverse Recovery Time	t _{RR}	_	19	_	ns	I _S = -11.5A, dl/dt = 100A/µs	
Reverse Recovery Charge	Q _{RR}	_	9.8	_	nC		

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

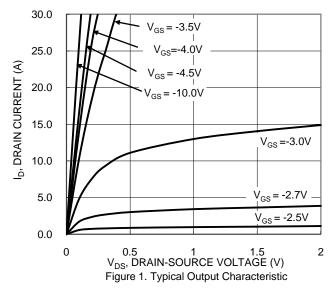
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} Thermal resistance from junction to soldering point (on the exposed drain pad).

^{8.} Ias and Eas rating are based on low frequency and duty cycles to keep $T_J = +25$ °C. 9. Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.





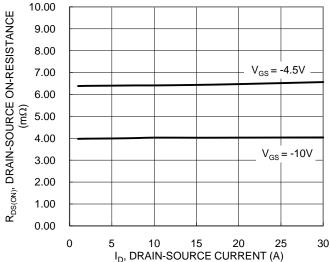


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

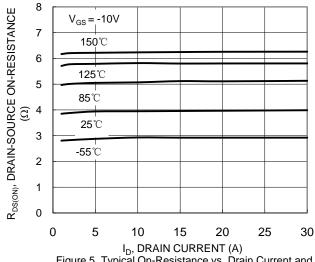
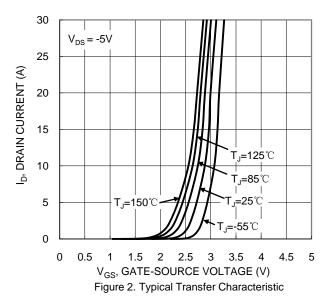
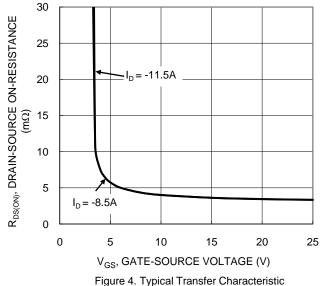


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





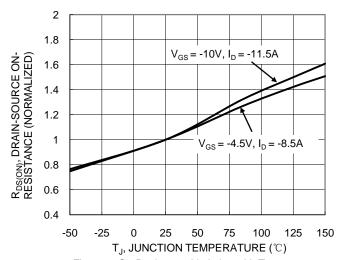


Figure 6. On-Resistance Variation with Temperature





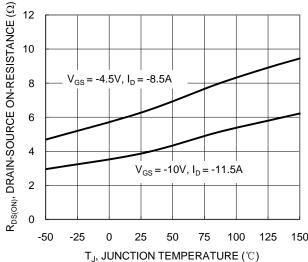
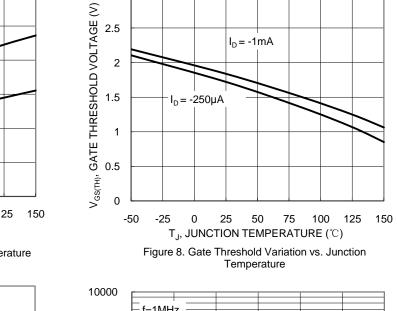
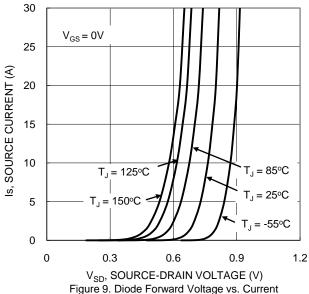
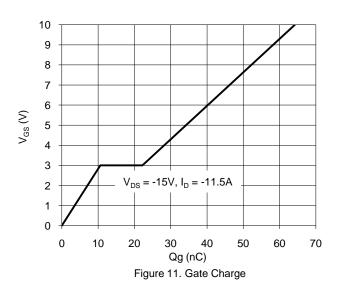


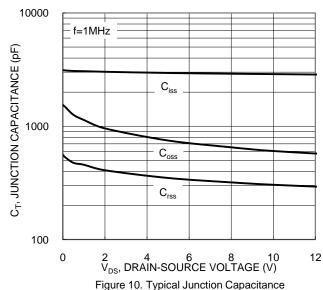
Figure 7. On-Resistance Variation with Temperature

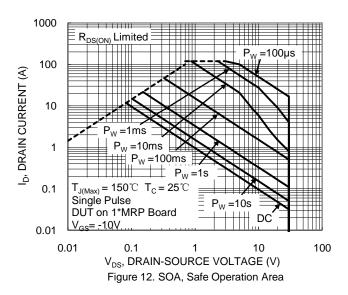


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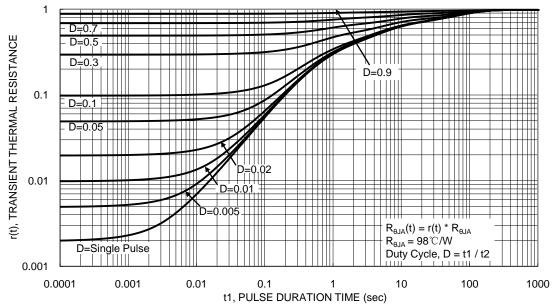


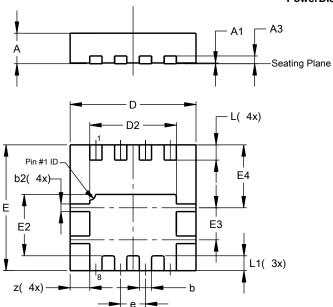
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

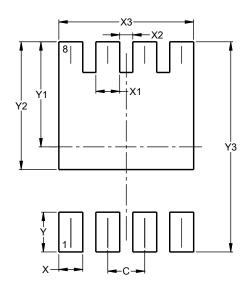


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	_	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3 700



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